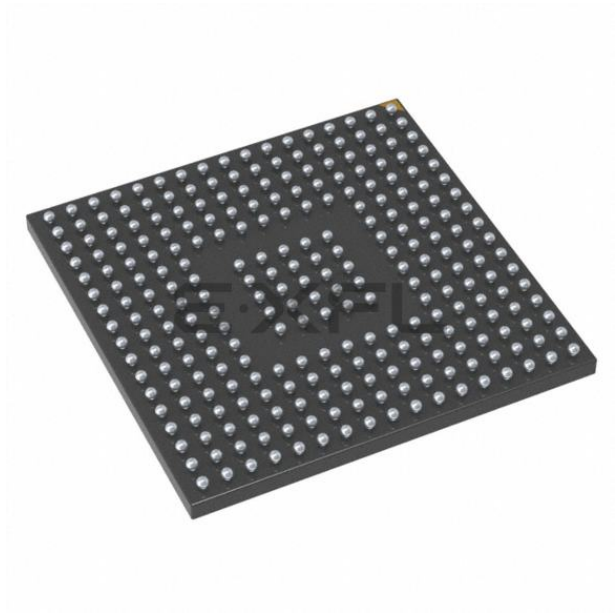

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, DCMI, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	140
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	201-UFBGA
Supplier Device Package	176+25UFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f407ieh7

2.2.5 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a software signature during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

2.2.6 Embedded SRAM

All STM32F40xxx products embed:

- Up to 192 Kbytes of system SRAM including 64 Kbytes of CCM (core coupled memory) data RAM

  RAM memory is accessed (read/write) at CPU clock speed with 0 wait states.
- 4 Kbytes of backup SRAM

  This area is accessible only from the CPU. Its content is protected against possible unwanted write accesses, and is retained in Standby or V_{BAT} mode.

2.2.7 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs, Ethernet, USB HS) and the slaves (Flash memory, RAM, FSMC, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.

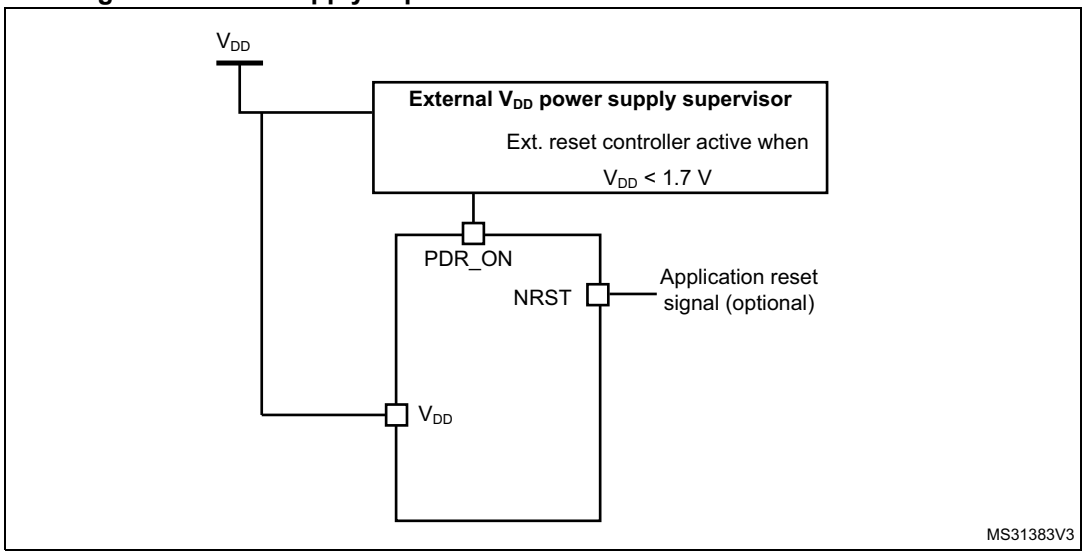
The device also features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

Internal reset OFF

This feature is available only on packages featuring the PDR_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled with the PDR_ON pin.

An external power supply supervisor should monitor V_{DD} and should maintain the device in reset mode as long as V_{DD} is below a specified threshold. PDR_ON should be connected to this external power supply supervisor. Refer to *Figure 7: Power supply supervisor interconnection with internal reset OFF*.

Figure 7. Power supply supervisor interconnection with internal reset OFF



1. PDR = 1.7 V for reduce temperature range; PDR = 1.8 V for all temperature range.

The V_{DD} specified threshold, below which the device must be maintained under reset, is 1.8 V (see *Figure 7*). This supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range.

A comprehensive set of power-saving mode allows to design low-power applications.

When the internal reset is OFF, the following integrated features are no more supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled
- The brownout reset (BOR) circuitry is disabled
- The embedded programmable voltage detector (PVD) is disabled
- V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD}

All packages, except for the LQFP64 and LQFP100, allow to disable the internal reset through the PDR_ON signal.

Table 7. STM32F40xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset)[1]	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
-	A8	-	143	C6	171	PDR_ON	I	FT	-	-	-
64	A1	100	144	C5	172	V_{DD}	S	-	-	-	-
-	-	-	-	D4	173	PI4	I/O	FT	-	TIM8_BKIN / DCMI_D5/ EVENTOUT	-
-	-	-	-	C4	174	PI5	I/O	FT	-	TIM8_CH1 / DCMI_VSYNC/ EVENTOUT	-
-	-	-	-	C3	175	PI6	I/O	FT	-	TIM8_CH2 / DCMI_D6/ EVENTOUT	-
-	-	-	-	C2	176	PI7	I/O	FT	-	TIM8_CH3 / DCMI_D7/ EVENTOUT	-

1. Function availability depends on the chosen device.
2. PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited:
   - The speed should not exceed 2 MHz with a maximum load of 30 pF.
   - These I/Os must not be used as a current source (e.g. to drive an LED).
3. Main function after the first backup domain power-up. Later on, it depends on the contents of the RTC registers even after reset (because these registers are not reset by the main reset). For details on how to manage these I/Os, refer to the RTC register description sections in the STM32F4xx reference manual, available from the STMicroelectronics website: *www.st.com*.
4. FT = 5 V tolerant except when in analog mode or oscillator mode (for PC14, PC15, PH0 and PH1).
5. If the device is delivered in an UFBGA176 or WLCSP90 and the BYPASS_REG pin is set to VDD (Regulator off/internal reset ON mode), then PA0 is used as an internal Reset (active low).

Table 8. FSMC pin definition

Pins[1]	FSMC				LQFP100[2]	WLCSP90 [2]
	CF	NOR/PSRAM/ SRAM	NOR/PSRAM Mux	NAND 16 bit		
PE2	-	A23	A23	-	Yes	-
PE3	-	A19	A19	-	Yes	-
PE4	-	A20	A20	-	Yes	-
PE5	-	A21	A21	-	Yes	-
PE6	-	A22	A22	-	Yes	-
PF0	A0	A0	-	-	-	-

Table 9. Alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/SPI2/I2S2/I2S2ext	SPI3/I2Sext/I2S3	USART1/2/3/I2S3ext	UART4/5/USART6	CAN1/2 TIM12/13/14	OTG_FS/OTG_HS	ETH	FSMC/SDIO/OTG_FS	DCMI		
Port I	PI0	-	-	TIM5_CH4	-	-	SPI2_NSS I2S2_WS	-	-	-	-	-	-	-	DCMI_D13	-	EVENTOUT
	PI1	-	-	-	-	-	SPI2_SCK I2S2_CK	-	-	-	-	-	-	-	DCMI_D8	-	EVENTOUT
	PI2	-	-	-	TIM8_CH4	-	SPI2_MISO	I2S2ext_SD	-	-	-	-	-	-	DCMI_D9	-	EVENTOUT
	PI3	-	-	-	TIM8_ETR	-	SPI2_MOSI I2S2_SD	-	-	-	-	-	-	-	DCMI_D10	-	EVENTOUT
	PI4	-	-	-	TIM8_BKIN	-	-	-	-	-	-	-	-	-	DCMI_D5	-	EVENTOUT
	PI5	-	-	-	TIM8_CH1	-	-	-	-	-	-	-	-	-	DCMI_VSYNC	-	EVENTOUT
	PI6	-	-	-	TIM8_CH2	-	-	-	-	-	-	-	-	-	DCMI_D6	-	EVENTOUT
	PI7	-	-	-	TIM8_CH3	-	-	-	-	-	-	-	-	-	DCMI_D7	-	EVENTOUT
	PI8	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PI9	-	-	-	-	-	-	-	-	-	CAN1_RX	-	-	-	-	-	EVENTOUT
	PI10	-	-	-	-	-	-	-	-	-	-	-	ETH _MII_RX_ER	-	-	-	EVENTOUT
	PI11	-	-	-	-	-	-	-	-	-	-	OTG_HS_ULPI_DIR	-	-	-	-	EVENTOUT

Table 10. register boundary addresses

Bus	Boundary address	Peripheral
	0xE00F FFFF - 0xFFFF FFFF	Reserved
Cortex-M4	0xE000 0000 - 0xE00F FFFF	Cortex-M4 internal peripherals
	0xA000 1000 - 0xDFFF FFFF	Reserved
AHB3	0xA000 0000 - 0xA000 0FFF	FSMC control register
	0x9000 0000 - 0x9FFF FFFF	FSMC bank 4
	0x8000 0000 - 0x8FFF FFFF	FSMC bank 3
	0x7000 0000 - 0x7FFF FFFF	FSMC bank 2
	0x6000 0000 - 0x6FFF FFFF	FSMC bank 1
	0x5006 0C00- 0x5FFF FFFF	Reserved
AHB2	0x5006 0800 - 0x5006 0BFF	RNG
	0x5005 0400 - 0x5006 07FF	Reserved
	0x5005 0000 - 0x5005 03FF	DCMI
	0x5004 0000- 0x5004 FFFF	Reserved
	0x5000 0000 - 0x5003 FFFF	USB OTG FS
	0x4008 0000- 0x4FFF FFFF	Reserved

5 Electrical characteristics

5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3Σ).

5.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.3 V (for the 1.8 V ≤V_{DD} ≤3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2Σ).

5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 19*.

5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 20*.

Figure 19. Pin loading conditions

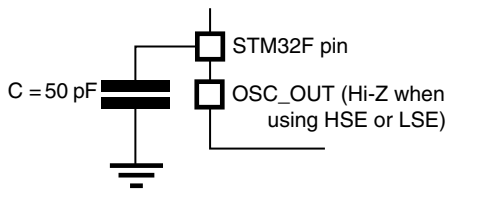
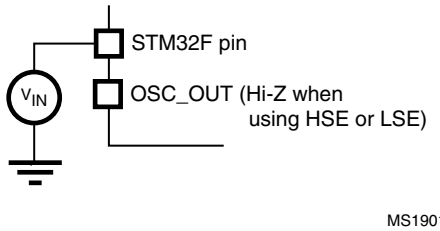


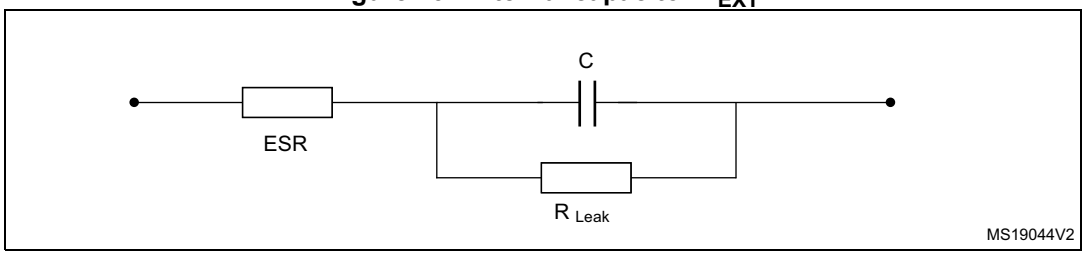
Figure 20. Pin input voltage



5.3.2 V_{CAP_1}/V_{CAP_2} external capacitor

Stabilization for the main regulator is achieved by connecting an external capacitor C_{EXT} to the V_{CAP_1}/V_{CAP_2} pins. C_{EXT} is specified in *Table 16*.

Figure 23. External capacitor C_{EXT}



1. Legend: ESR is the equivalent series resistance.

Table 16. V_{CAP_1}/V_{CAP_2} operating conditions(1)

Symbol	Parameter	Conditions
CEXT	Capacitance of external capacitor	2.2 µF
ESR	ESR of external capacitor	< 2 Ω

1. When bypassing the voltage regulator, the two 2.2 µF V_{CAP} capacitors are not required and should be replaced by two 100 nF decoupling capacitors.

5.3.3 Operating conditions at power-up / power-down (regulator ON)

Subject to general operating conditions for T_A.

Table 17. Operating conditions at power-up / power-down (regulator ON)

Symbol	Parameter	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	20	∞	µs/V
	V_{DD} fall time rate	20	∞	

5.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A.

Table 18. Operating conditions at power-up / power-down (regulator OFF)(1)

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	µs/V
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when V_{DD} reach below minimum value of V_{12}.

Table 20. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM (1)

Symbol	Parameter	Conditions	f_{HCLK}	Typ	Max(2)		Unit
				T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in Run mode	External clock(3), all peripherals enabled(4)(5)	168 MHz	87	102	109	mA
			144 MHz	67	80	86	
			120 MHz	56	69	75	
			90 MHz	44	56	62	
			60 MHz	30	42	49	
			30 MHz	16	28	35	
			25 MHz	12	24	31	
			16 MHz(6)	9	20	28	
			8 MHz	5	17	24	
			4 MHz	3	15	22	
			2 MHz	2	14	21	
		External clock(3), all peripherals disabled(4)(5)	168 MHz	40	54	61	
			144 MHz	31	43	50	
			120 MHz	26	38	45	
			90 MHz	20	32	39	
			60 MHz	14	26	33	
			30 MHz	8	20	27	
			25 MHz	6	18	25	
			16 MHz(6)	5	16	24	
			8 MHz	3	15	22	
			4 MHz	2	14	21	
			2 MHz	2	14	21	

1. Code and data processing running from SRAM1 using boot pins.
2. Guaranteed by characterization, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.
3. External clock is 4 MHz and PLL is on when f_{HCLK} > 25 MHz.
4. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.
5. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
6. In this case HCLK = system clock/2.

Table 28. Peripheral current consumption (continued)

Peripheral		I_{DD}(Typ)(1)		Unit
		Scale1 (up t 168 MHz)	Scale2 (up to 144 MHz)	
AHB2 (up to 168 MHz)	OTG_FS	26.45	26.67	µA/MHz
	DCMI	5.87	5.35	
	RNG	1.50	1.67	
AHB3 (up to 168 MHz)	FSMC	12.46	11.31	µA/MHz
Bus matrix(2)		13.10	11.81	µA/MHz
APB1 (up to 42 MHz)	TIM2	16.71	16.50	µA/MHz
	TIM3	12.33	11.94	
	TIM4	13.45	12.92	
	TIM5	17.14	16.58	
	TIM6	2.43	3.06	
	TIM7	2.43	2.22	
	TIM12	6.62	6.83	
	TIM13	5.05	5.47	
	TIM14	5.26	5.61	
	PWR	1.00	0.56	
	USART2	2.69	2.78	
	USART3	2.74	2.78	
	UART4	3.24	3.33	
	UART5	2.69	2.78	
	I2C1	2.67	2.50	
	I2C2	2.83	2.78	
	I2C3	2.81	2.78	
	SPI2	2.43	2.22	
	SPI3	2.43	2.22	
	I2S2(3)	2.43	2.22	
	I2S3(3)	2.26	2.22	
	CAN1	5.12	5.56	
	CAN2	4.81	5.28	
	DAC(4)	1.67	1.67	
	WWDG	1.00	0.83	

Table 28. Peripheral current consumption (continued)

Peripheral		I_{DD}(Typ)(1)		Unit
		Scale1 (up t 168 MHz)	Scale2 (up to 144 MHz)	
APB2 (up to 84 MHz)	SDIO	7.08	7.92	µA/MHz
	TIM1	16.79	15.51	
	TIM8	17.88	16.53	
	TIM9	7.64	7.28	
	TIM10	4.89	4.82	
	TIM11	5.19	4.82	
	ADC1(5)	4.67	4.58	
	ADC2(5)	4.67	4.58	
	ADC3(5)	4.43	4.44	
	SPI1	1.32	1.39	
	USART1	3.51	3.72	
	USART6	3.55	3.75	
	SYSCFG	0.74	0.56	

1. When the I/O compensation cell is ON, I_{DD} typical value increases by 0.22 mA.
2. The BusMatrix is automatically active when at least one master is ON.
3. To enable an I2S peripheral, first set the I2SMOD bit and then the I2SE bit in the SPI_I2SCFGR register.
4. When the DAC is ON and EN1/2 bits are set in DAC_CR register, add an additional power consumption of 0.8 mA per DAC channel for the analog part.
5. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

5.3.7 Wakeup time from low-power mode

The wakeup times given in *Table 29* is measured on a wakeup phase with a 16 MHz HSI RC oscillator. The clock source used to wake up the device depends from the current operating mode:

- Stop or Standby mode: the clock source is the RC oscillator
- Sleep mode: the clock source is the clock that was set before entering Sleep mode.

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 29. Low-power mode wakeup timings

Symbol	Parameter	Min(1)	Typ(1)	Max(1)	Unit
$t_{WUSLEEP}$(2)	Wakeup from Sleep mode	-	5	-	CPU clock cycle
t_{WUSTOP}(2)	Wakeup from Stop mode (regulator in Run mode and Flash memory in Stop mode)	-	13	-	µs
	Wakeup from Stop mode (regulator in low-power mode and Flash memory in Stop mode)	-	17	40	
	Wakeup from Stop mode (regulator in Run mode and Flash memory in Deep power-down mode)	-	105	-	
	Wakeup from Stop mode (regulator in low-power mode and Flash memory in Deep power-down mode)	-	110	-	
$t_{WUSTDBY}$(2)(3)	Wakeup from Standby mode	260	375	480	µs

1. Guaranteed by characterization.
2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first instruction.
3. $t_{WUSTDBY}$ minimum and maximum values are given at 105 °C and –45 °C, respectively.

5.3.8 External clock source characteristics

High-speed external user clock generated from an external source

The characteristics given in *Table 30* result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 14*.

Table 30. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	External user clock source frequency(1)	-	1	-	50	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time(1)		5	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time(1)		-	-	10	
$C_{in(HSE)}$	OSC_IN input capacitance(1)	-	-	5	-	pF
$DuCy_{(HSE)}$	Duty cycle	-	45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design.

Table 55. SPI dynamic characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{w(SCKH)}$	SCK high and low time	Master mode, SPI presc = 2, 2.7V < V_{DD} < 3.6V	T_{PCLK}-0.5	T_{PCLK}	T_{PCLK}+0.5	ns
$t_{w(SCKL)}$		Master mode, SPI presc = 2, 1.7V < V_{DD} < 3.6V	T_{PCLK}-2	T_{PCLK}	T_{PCLK}+2	
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	4 x T_{PCLK}	-	-	
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	2 x T_{PCLK}			
$t_{su(MI)}$	Data input setup time	Master mode	6.5	-	-	
$t_{su(SI)}$		Slave mode	2.5	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	2.5	-	-	
$t_{h(SI)}$		Slave mode	4	-	-	
$t_{a(SO)}$(2)	Data output access time	Slave mode, SPI presc = 2	0	-	4 x T_{PCLK}	
$t_{dis(SO)}$(3)	Data output disable time	Slave mode, SPI1, 2.7V < V_{DD} < 3.6V	0	-	7.5	
		Slave mode, SPI1/2/3 1.7V < V_{DD} < 3.6V	0	-	16.5	
$t_{v(SO)}$ $t_{h(SO)}$	Data output valid/hold time	Slave mode (after enable edge), SPI1, 2.7V < V_{DD} < 3.6V	-	11	13	
		Slave mode (after enable edge), SPI2/3, 2.7V < V_{DD} < 3.6V	-	12	16.5	
		Slave mode (after enable edge), SPI1, 1.7V < V_{DD} < 3.6V	-	15.5	19	
		Slave mode (after enable edge), SPI2/3, 1.7V < V_{DD} < 3.6V	-	18	20.5	
$t_{v(MO)}$	Data output valid time	Master mode (after enable edge), SPI1, 2.7V < V_{DD} < 3.6V	-	-	2.5	
		Master mode (after enable edge), SPI1/2/3, 1.7V < V_{DD} < 3.6V	-	-	4.5	
$t_{h(MO)}$	Data output hold time	Master mode (after enable edge)	0	-	-	

1. Guaranteed by characterization.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z.

Table 79. Synchronous multiplexed NOR/PSRAM read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	$2T_{HCLK}$	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x=0..2)	-	0	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x= 0…2)	2	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	2	ns
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	2	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x=16…25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x=16…25)	0	-	ns
$t_{d(CLKL-NOEL)}$	FSMC_CLK low to FSMC_NOE low	-	0	ns
$t_{d(CLKL-NOEH)}$	FSMC_CLK low to FSMC_NOE high	2	-	ns
$t_{d(CLKL-ADV)}$	FSMC_CLK low to FSMC_AD[15:0] valid	-	4.5	ns
$t_{d(CLKL-ADIV)}$	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	ns
$t_{su(ADV-CLKH)}$	FSMC_A/D[15:0] valid data before FSMC_CLK high	6	-	ns
$t_{h(CLKH-ADV)}$	FSMC_A/D[15:0] valid data after FSMC_CLK high	0	-	ns
$t_{su(NWAIT-CLKH)}$	FSMC_NWAIT valid before FSMC_CLK high	4	-	ns
$t_{h(CLKH-NWAIT)}$	FSMC_NWAIT valid after FSMC_CLK high	0	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization.

Figure 59. Synchronous multiplexed PSRAM write timings

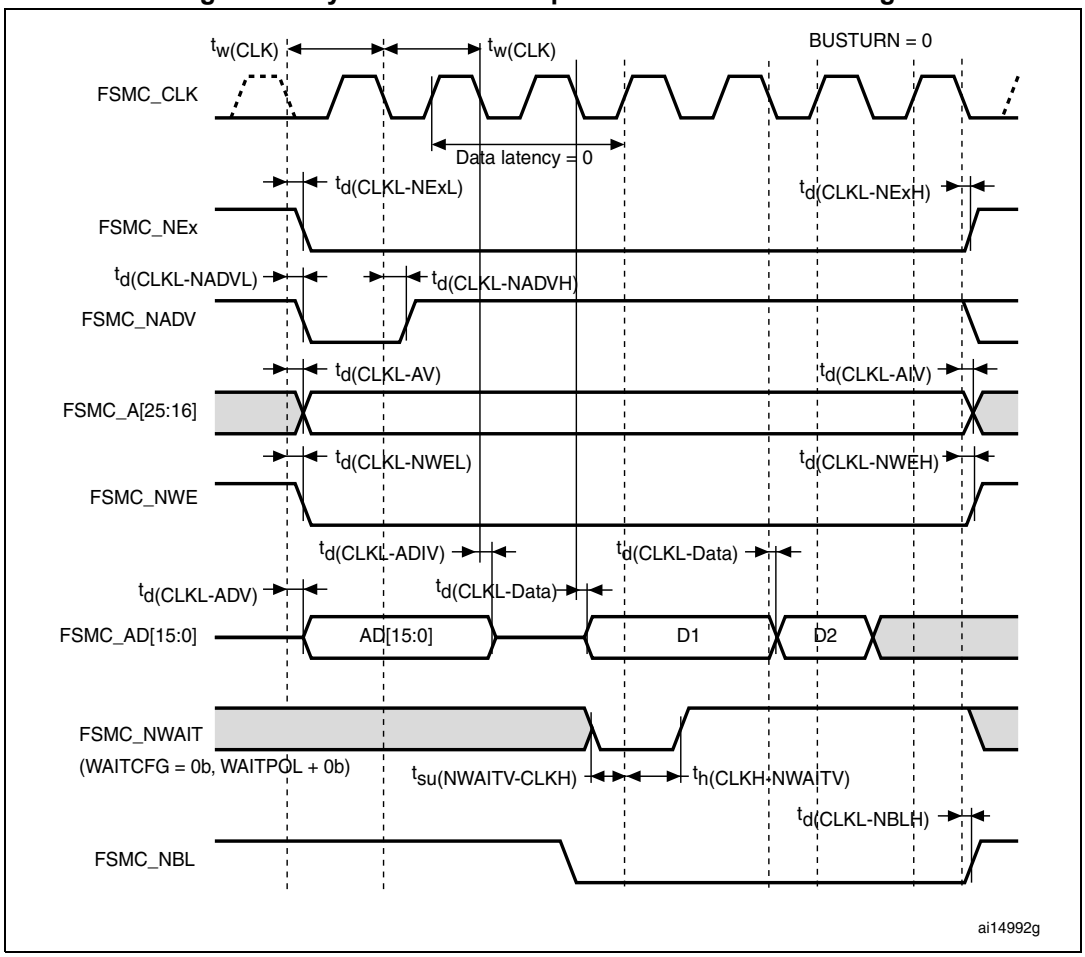


Table 80. Synchronous multiplexed PSRAM write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	$2T_{HCLK}$	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x=0..2)	-	1	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x= 0…2)	1	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	0	ns
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	0	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x=16…25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x=16…25)	8	-	ns
$t_{d(CLKL-NWEL)}$	FSMC_CLK low to FSMC_NWE low	-	0.5	ns
$t_{d(CLKL-NWEH)}$	FSMC_CLK low to FSMC_NWE high	0	-	ns
$t_{d(CLKL-ADIV)}$	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	ns
$t_{d(CLKL-DATA)}$	FSMC_A/D[15:0] valid data after FSMC_CLK low	-	3	ns

Table 86. Switching characteristics for NAND Flash write cycles(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NWE)}$	FSMC_NWE low width	$4T_{HCLK}-1$	$4T_{HCLK}+3$	ns
$t_{v(NWE-D)}$	FSMC_NWE low to FSMC_D[15-0] valid	-	0	ns
$t_{h(NWE-D)}$	FSMC_NWE high to FSMC_D[15-0] invalid	$3T_{HCLK}-2$	-	ns
$t_{d(D-NWE)}$	FSMC_D[15-0] valid before FSMC_NWE high	$5T_{HCLK}-3$	-	ns
$t_{d(ALE-NWE)}$	FSMC_ALE valid before FSMC_NWE low	-	$3T_{HCLK}$	ns
$t_{h(NWE-ALE)}$	FSMC_NWE high to FSMC_ALE invalid	$3T_{HCLK}-2$	-	ns

1. C_L = 30 pF.

5.3.27 Camera interface (DCMI) timing specifications

Unless otherwise specified, the parameters given in *Table 87* for DCMI are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage summarized in *Table 13*, with the following configuration:

- PCK polarity: falling
- VSYNC and HSYNC polarity: high
- Data format: 14 bits

Figure 72. DCMI timing diagram

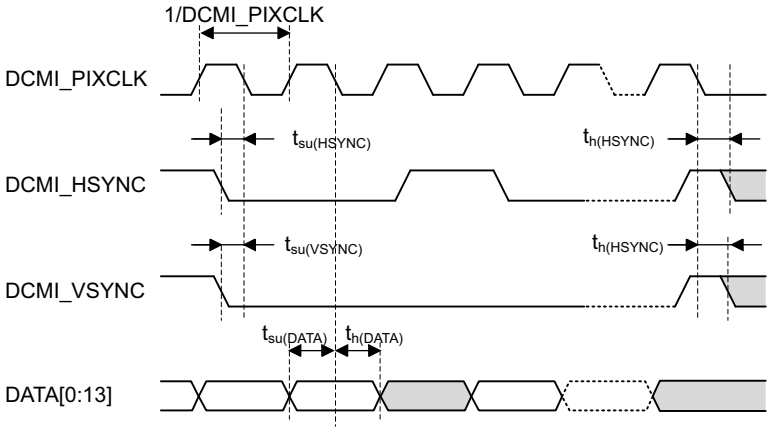
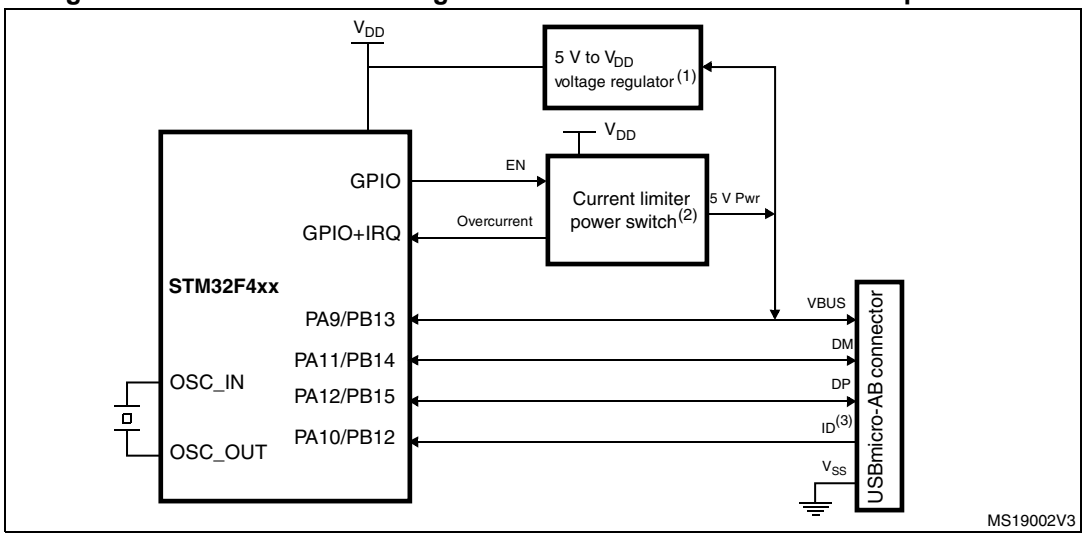


Table 87. DCMI characteristics(1)

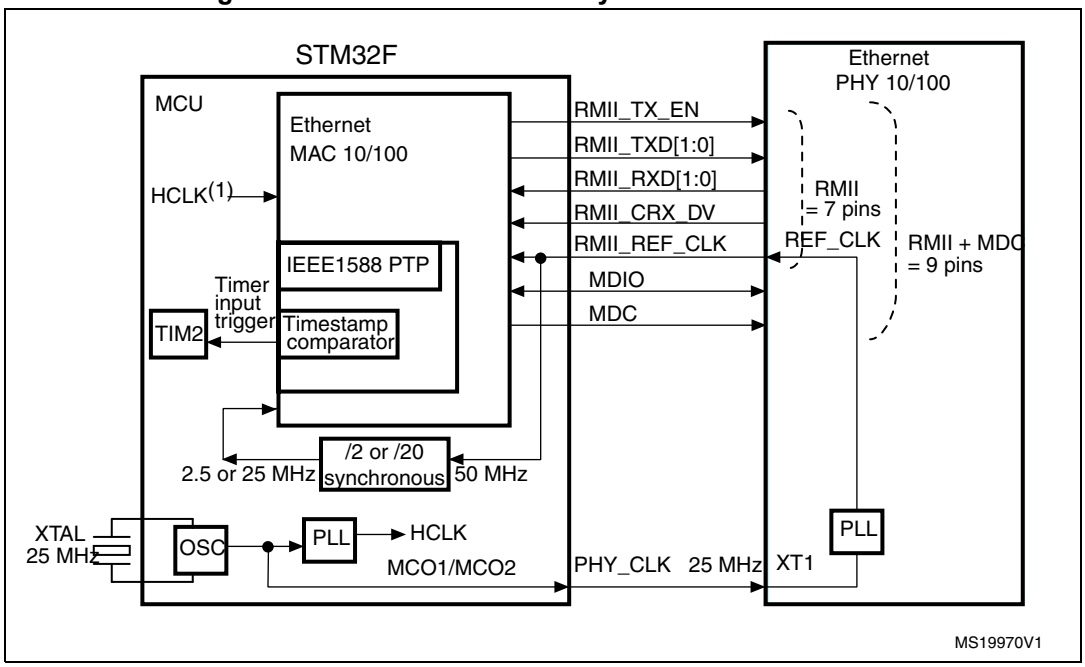
Symbol	Parameter	Min	Max	Unit
	Frequency ratio DCMI_PIXCLK/f_{HCLK}	-	0.4	
DCMI_PIXCLK	Pixel clock input	-	54	MHz
D_{pixel}	Pixel clock input duty cycle	30	70	%

Figure 95. USB controller configured in dual mode and used in full speed mode



1. External voltage regulator only needed when building a V_{BUS} powered device.
2. The current limiter is required only if the application has to support a V_{BUS} powered device. A basic power switch can be used if 5 V are available on the application board.
3. The ID pin is required in dual role only.
4. The same application can be developed using the OTG HS in FS mode to achieve enhanced performance thanks to the large Rx/Tx FIFO and to a dedicated DMA controller.

Figure 99. RMII with a 25 MHz crystal and PHY with PLL



1. f_{HCLK} must be greater than 25 MHz.
2. The 25 MHz (PHY_CLK) must be derived directly from the HSE oscillator, before the PLL block.

Table 100. Document revision history (continued)

Date	Revision	Changes
04-Jun-2013	4 (continued)	Updated *Figure 6: Multi-AHB matrix*. Updated *Figure 7: Power supply supervisor interconnection with internal reset OFF* Changed 1.2 V to V_{12} in *Section : Regulator OFF* Updated LQFP176 pin 48. Updated *Section 1: Introduction*. Updated *Section 2: Description*. Updated operating voltage in *Table 2: STM32F405xx and STM32F407xx: features and peripheral counts*. Updated *Note 1*. Updated *Section 2.2.15: Power supply supervisor*. Updated *Section 2.2.16: Voltage regulator*. Updated *Figure 9: Regulator OFF*. Updated *Table 3: Regulator ON/OFF and internal reset ON/OFF availability*. Updated *Section 2.2.19: Low-power modes*. Updated *Section 2.2.20: VBAT operation*. Updated *Section 2.2.22: Inter-integrated circuit interface (I²C)* . Updated pin 48 in *Figure 15: STM32F40xxx LQFP176 pinout*. Updated *Table 6: Legend/abbreviations used in the pinout table*. Updated *Table 7: STM32F40xxx pin and ball definitions*. Updated *Table 14: General operating conditions*. Updated *Table 15: Limitations depending on the operating power supply range*. Updated *Section 5.3.7: Wakeup time from low-power mode*. Updated *Table 34: HSI oscillator characteristics*. Updated *Section 5.3.15: I/O current injection characteristics*. Updated *Table 48: I/O static characteristics*. Updated *Table 51: NRST pin characteristics*. Updated *Table 56: I^2C characteristics*. Updated *Figure 39: I^2C bus AC waveforms and measurement circuit*. Updated *Section 5.3.19: Communications interfaces*. Updated *Table 67: ADC characteristics*. Added *Table 70: Temperature sensor calibration values*. Added *Table 73: Internal reference voltage calibration values*. Updated *Section 5.3.26: FSMC characteristics*. Updated *Section 5.3.28: SD/SDIO MMC card host interface (SDIO) characteristics*. Updated *Table 23: Typical and maximum current consumptions in Stop mode*. Updated *Section : SPI interface characteristics* included *Table 55*. Updated *Section : I2S interface characteristics* included *Table 56*. Updated *Table 64: Dynamic characteristics: Eternity MAC signals for SMI*. Updated *Table 66: Dynamic characteristics: Ethernet MAC signals for MII*.